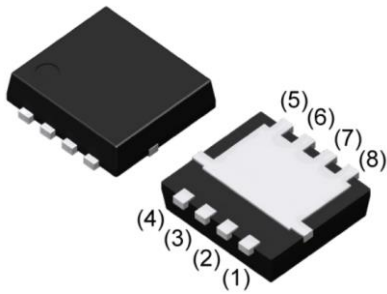


Description
30V N-CHANNEL ENHANCEMENT MODE POWER MOSFET
Features

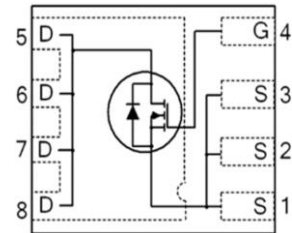
- Device Rating $V_{DS} = 30V$, $I_D = 155A$
- $R_{DS(ON)} = 1.6m\Omega$ (max.) @ $V_{GS} = 10V$, $I_D = 10A$
- Proprietary High Density Trench Technology
- RoHS Compliant & Halogen-Free

Application

- Battery Management System
- Load Switch
- Brushless DC Motor Control

Package


DFN3*3-8L
JFG155N30K


Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise specified

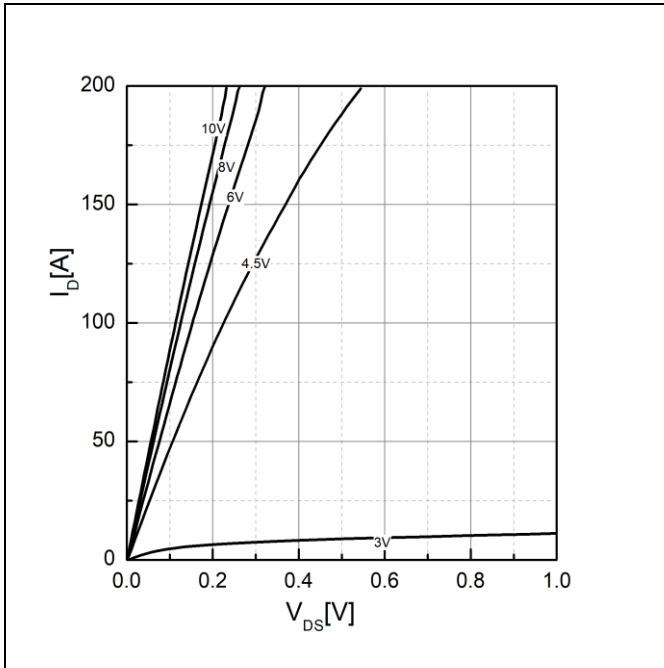
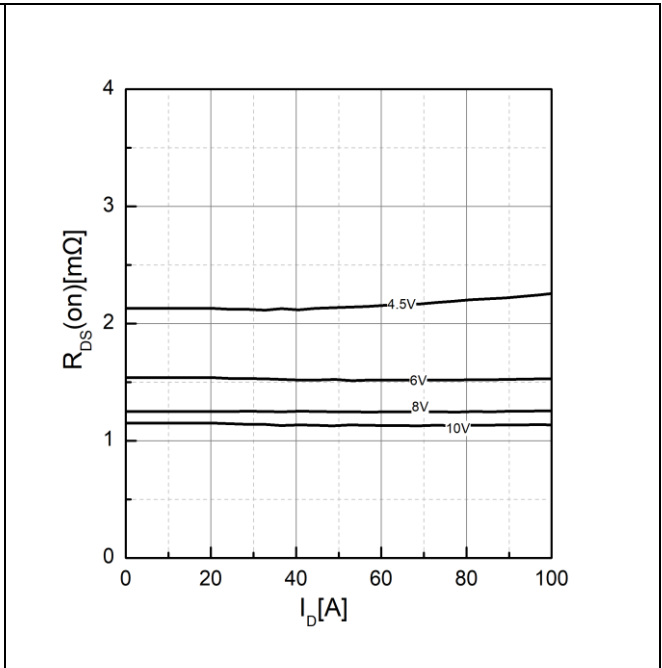
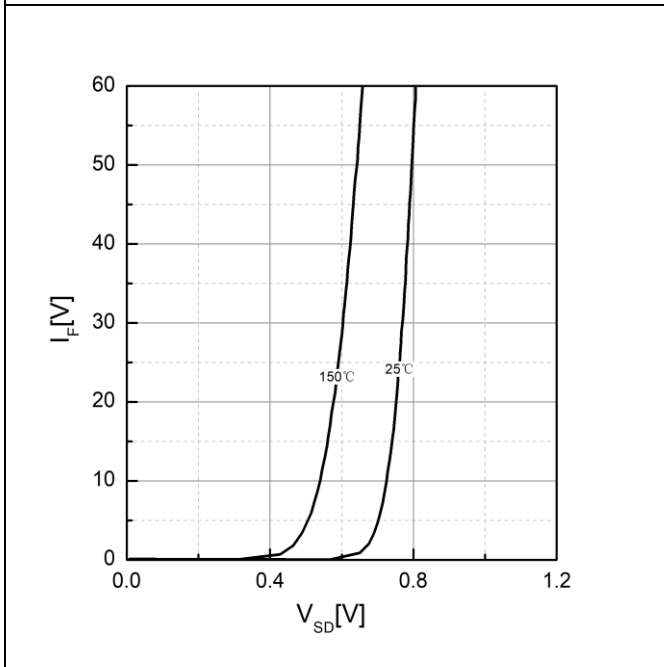
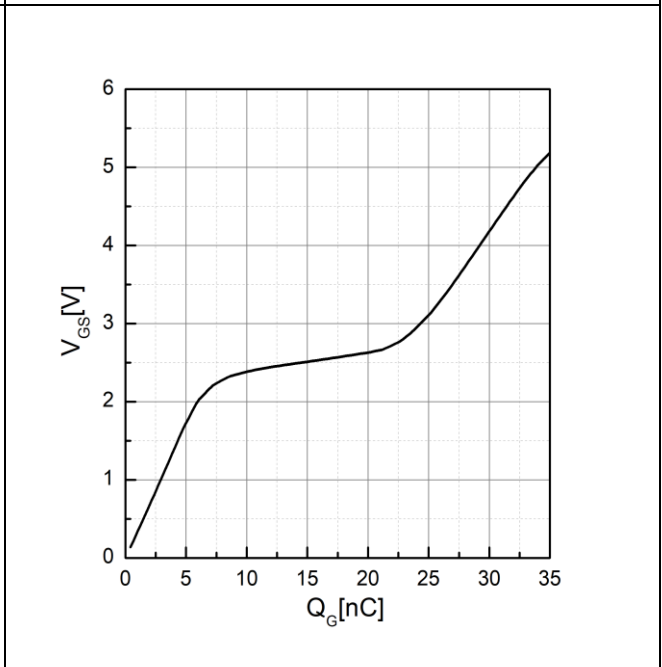
Symbol	Parameter	Max.	Units	
V_{DS}	Drain-Source Voltage	30	V	
V_{GS}	Gate-Source Voltage	± 20	V	
I_D	Continuous Drain Current, $V_{GS} @ 10V$ ^{note1}	$T_C = 25^\circ C$	155	A
		$T_C = 100^\circ C$	98	A
I_{DM}	Pulsed Drain Current ^{note2}	620	A	
P_D	Power Dissipation ^{note4}	$T_C = 25^\circ C$	61	W
	Power Dissipation	$T_A = 25^\circ C$	3.57	W
E_{AS}	Single Pulsed Avalanche Energy ^{note3}	200	mJ	
$R_{\theta JC}$	Thermal Resistance, Junction to Case ^{note1}	2.05	$^\circ C/W$	
$R_{\theta JA}$	Junction-to-Ambient (mounted on 1 inch square PCB)	35	$^\circ C/W$	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$	

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-100	-	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	-	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^{note2}	$V_{GS} = 10V, I_D = 10A$	-	1.27	1.6	m Ω
		$V_{GS} = 4.5V, I_D = 10A$	-	2.17	3.0	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 5V, I_D = 30A$	-	164	-	S
Dynamic Characteristics						
R_g	Gate Resistance		-	1.4	-	Ω
C_{iss}	Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	2960	-	pF
C_{oss}	Output Capacitance		-	631	-	pF
C_{rss}	Reverse Transfer Capacitance		-	561	-	pF
Q_g	Total Gate Charge	$V_{DD} = 15V, I_D = 20A,$ $V_{GS} = 4.5V$	-	32	-	nC
Q_{gs}	Gate-Source Charge		-	7.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	18.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15V, I_D = 30A,$ $R_G = 3\Omega, V_{GS} = 10V$	-	50	-	ns
t_r	Turn-On Rise Time		-	80	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	70	-	ns
t_f	Turn-Off Fall Time		-	56	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Diode Forward Current ^{note1,5}		-	-	50	A
I_{SM}	Maximum Pulsed Diode Forward Current ^{note2,5}		-	-	620	A
t_{rr}	Reverse Recovery Time	$T_J = 25^{\circ}\text{C}, I_F = 30A,$ $di/dt = 100A/\mu s$	-	38	-	ns
Q_{rr}	Reverse Recovery Charge	$T_J = 25^{\circ}\text{C}, I_F = 30A,$ $di/dt = 100A/\mu s$	-	16	-	nC
V_{SD} ^{note2}	Drain to Source Diode Forward Voltage	$T_J = 25^{\circ}\text{C}, I_S = 20A,$ $V_{GS} = 0V$	-	0.76	1.2	V

Note :

- 1.The data tested by surface mounted on one inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating. The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=63.3A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Performance Characteristics

Figure 1. Output Characteristics, T_J=25°C

Figure 2. Drain-source on resistance , T_J=25°C

Figure 3. Forward characteristics of body diode

Figure 4. Gate Charge Characteristics

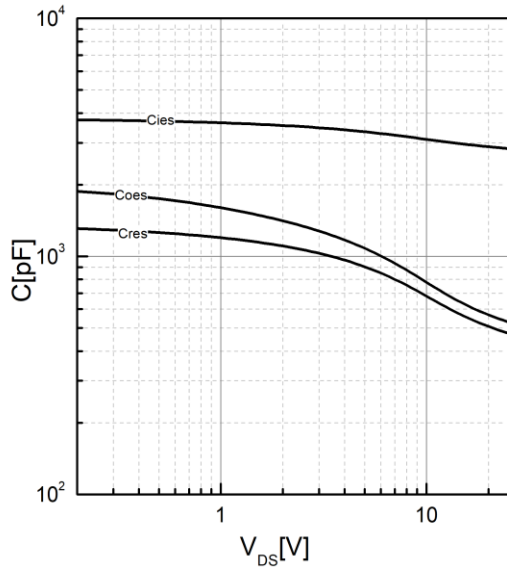


Figure 5. Capacitance Characteristics

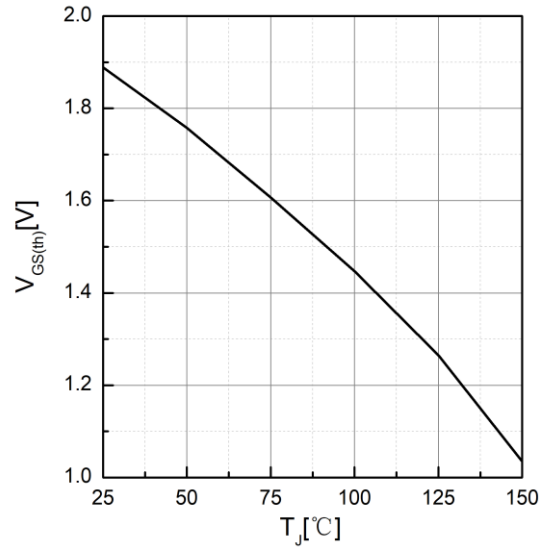


Figure 6. Threshold Voltage Vs. Temperature

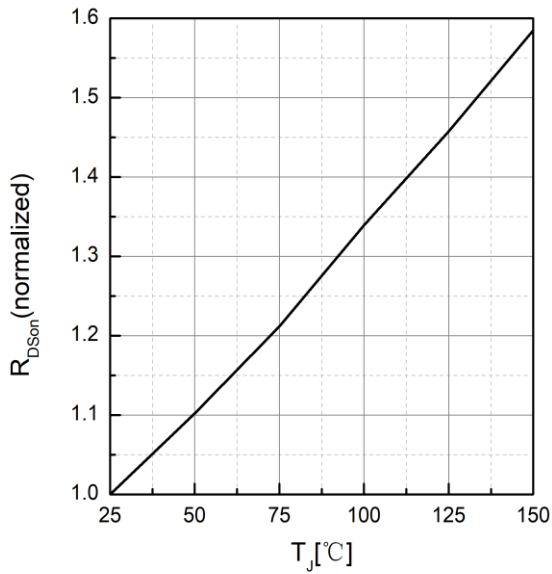


Figure 7. Drain-source on-state resistance

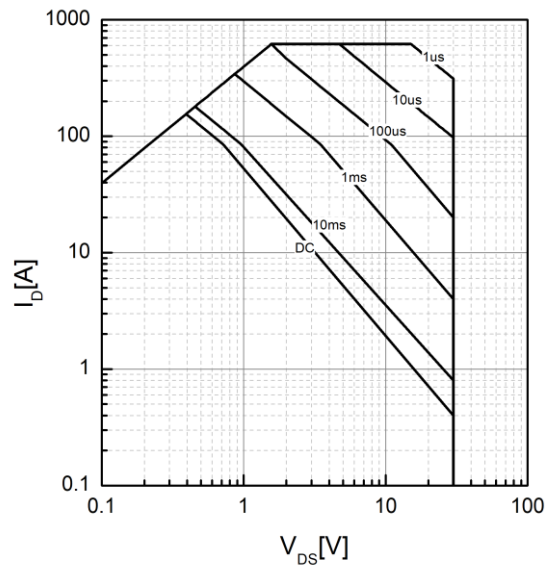


Figure 8. Maximum Safe Operating Area

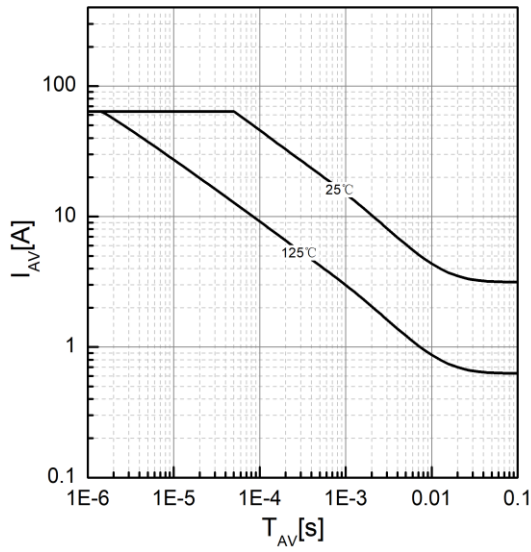


Figure 9. Avalanche characteristics

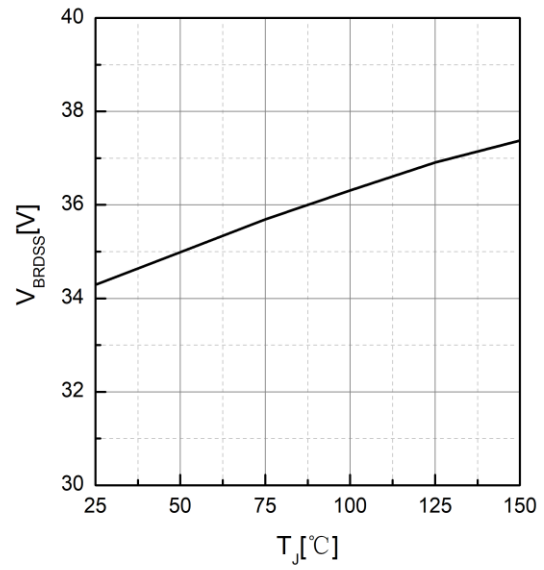


Figure 10. Drain-source breakdown voltage

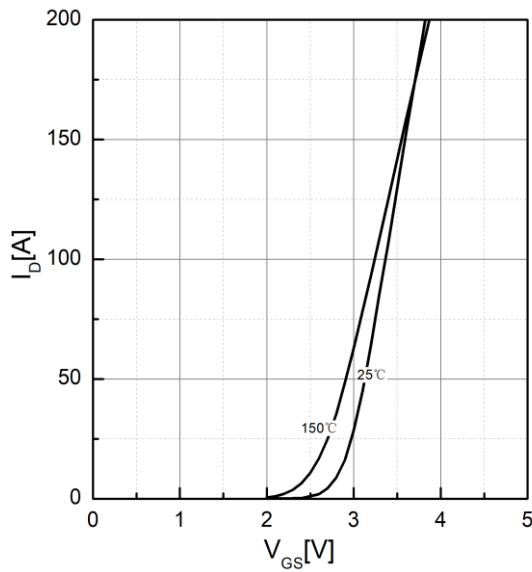


Figure 11. Transfer characteristics

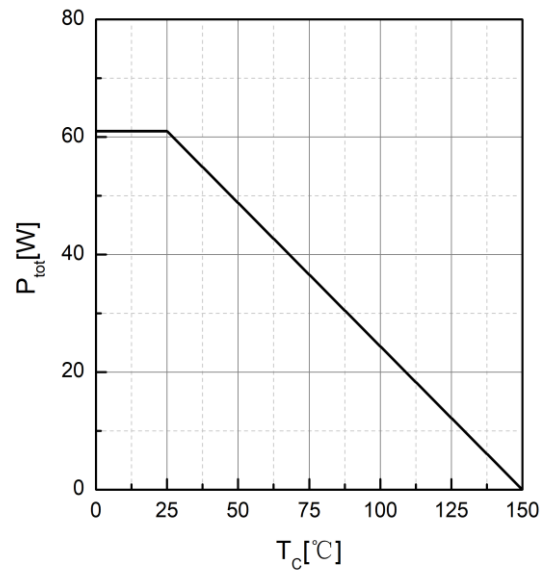


Figure 12. Power dissipation

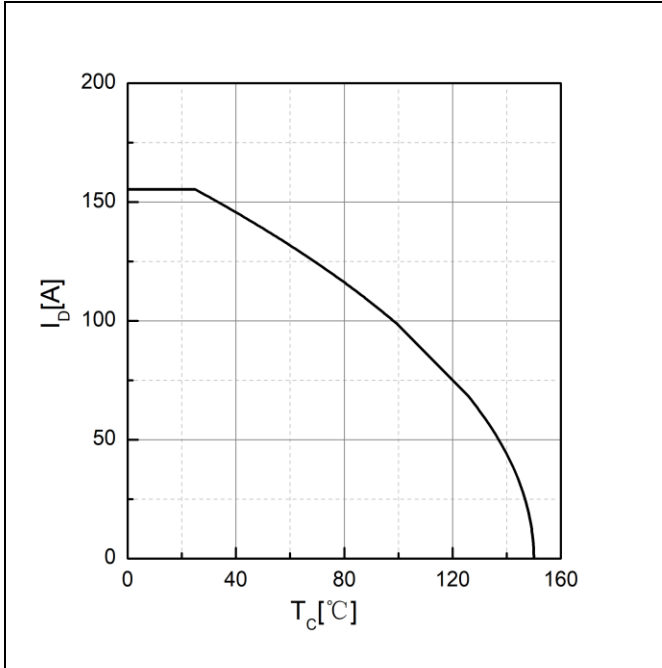


Figure 13. Drain current

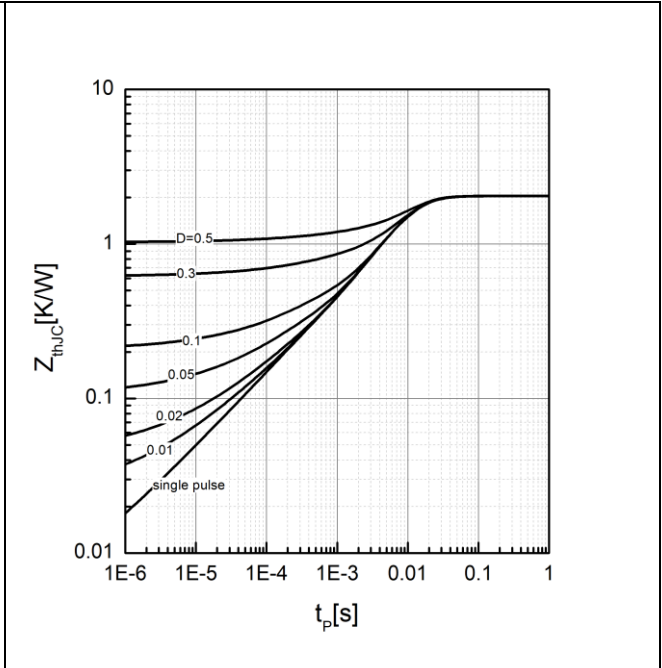


Figure 14. Effective Transient Thermal Impedance

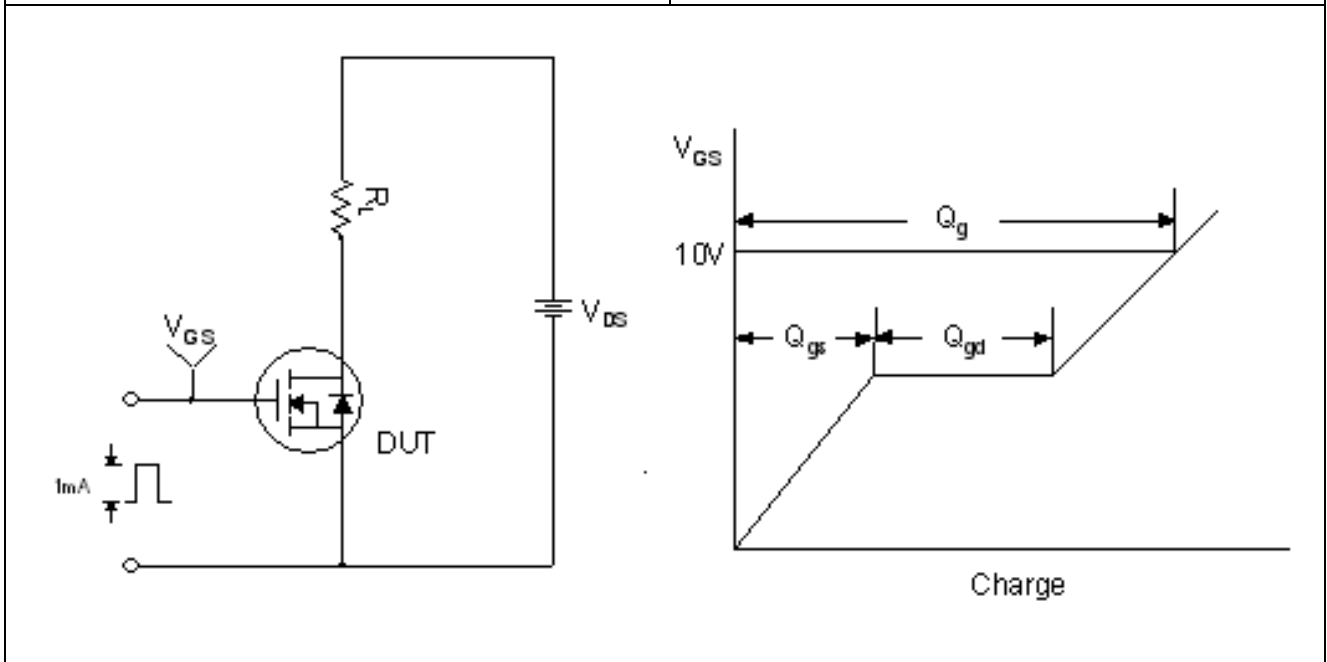


Figure 15. Gate Charge Test Circuit & Waveform

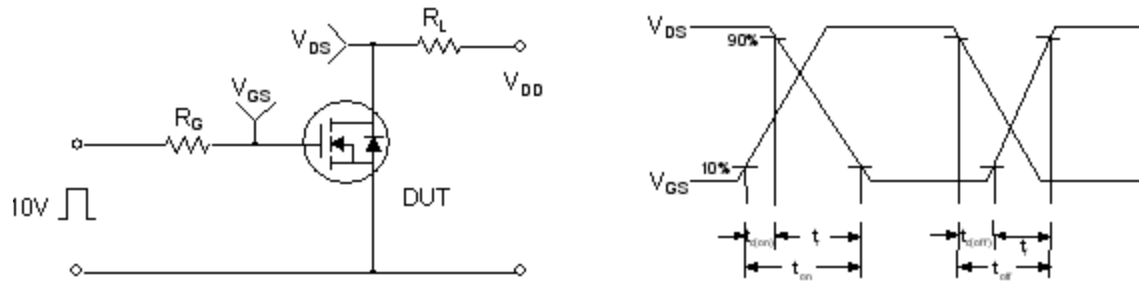


Figure 16. Resistive Switching Test Circuit & Waveforms

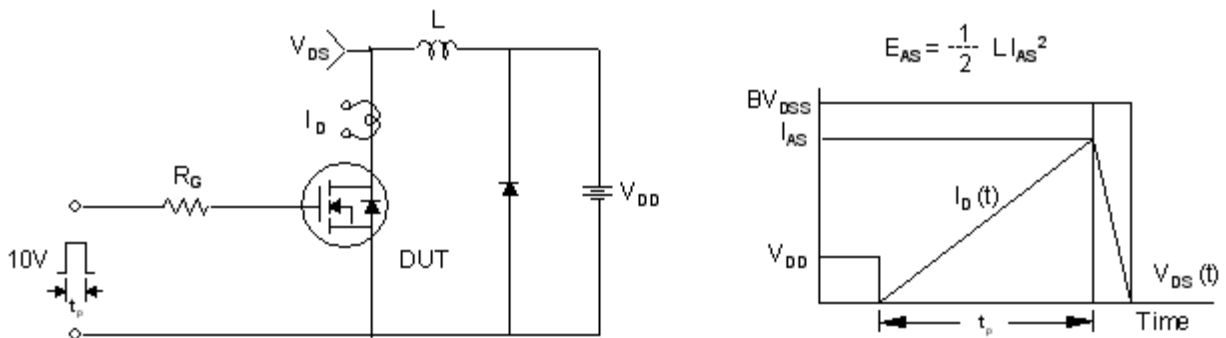


Figure 17. Unclamped Inductive Switching Test Circuit & Waveforms

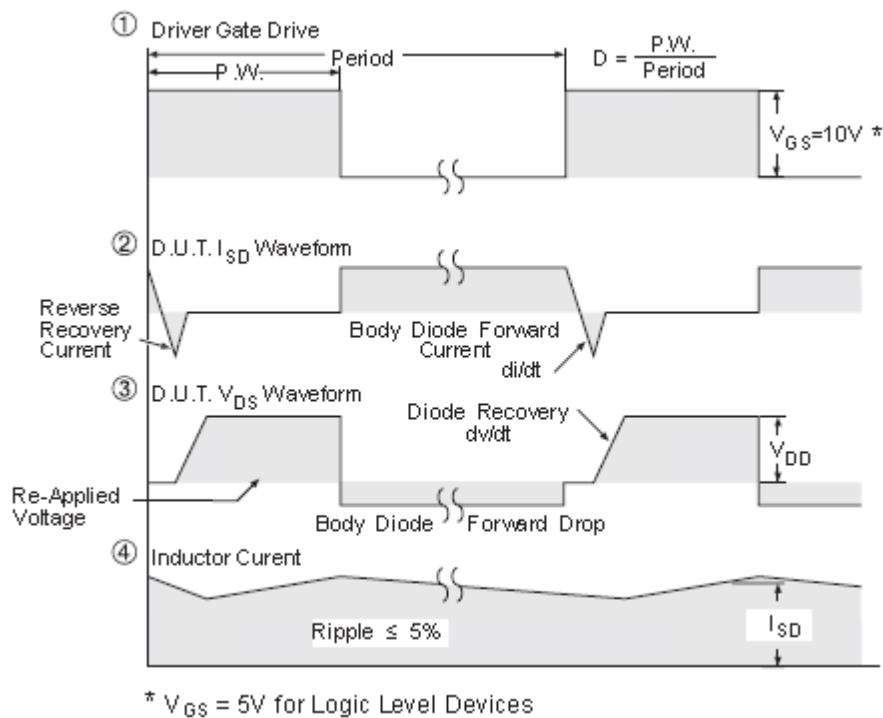
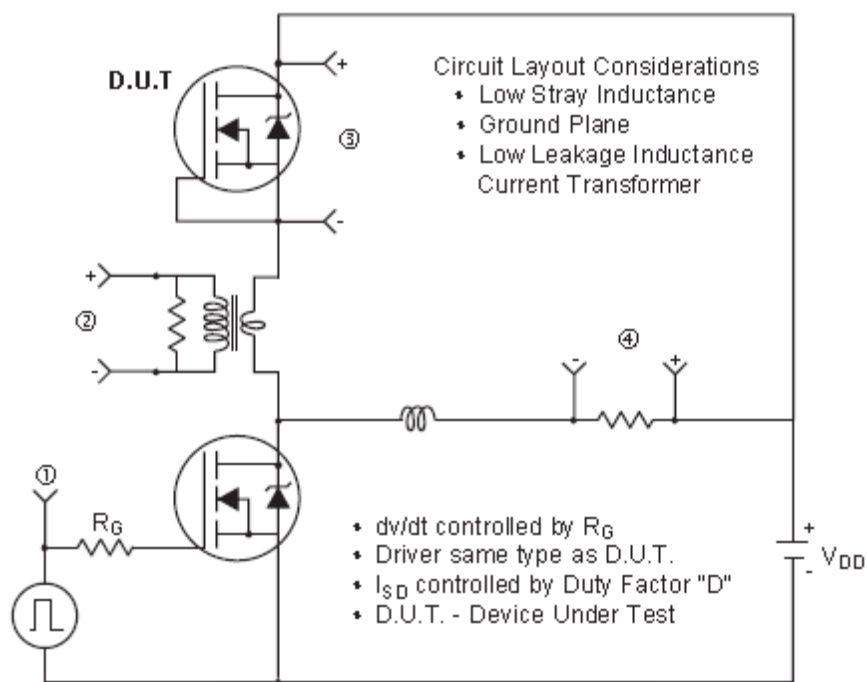


Figure 18. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

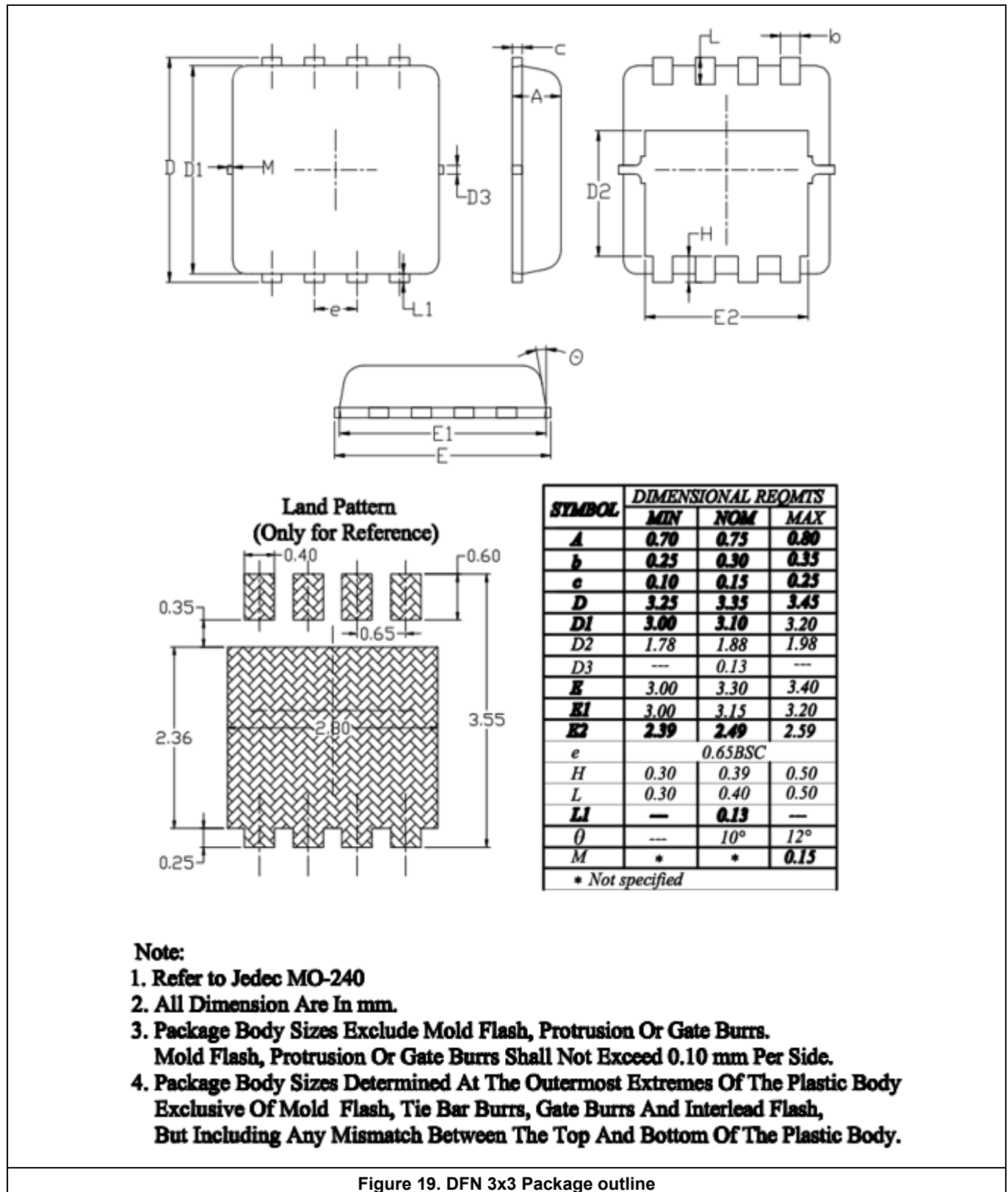
Package outline


Figure 19. DFN 3x3 Package outline

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